

01-20-04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

TRANSMITTAL FORM (to be used for all correspondence after initial filing)	Application Number	10/671,229
	Filing Date	September 24, 2003
	First Named Inventor	Leonard Forbes
	Art Unit	2811
	Examiner Name	Unknown
Total Number of Pages in This Submission	Attorney Docket Number	MI22-2272

ENCLOSURES (Check all that apply)		
<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input type="checkbox"/> Amendment/Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input checked="" type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation <input type="checkbox"/> Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s) _____	<input type="checkbox"/> After Allowance communication to Technology Center (TC) <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to TC (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input checked="" type="checkbox"/> Other Enclosure(s) (please identify below): Return Postcard PTO-1449 Cited references
Remarks Customer No. 021567 The Commissioner is hereby authorized to charge any additional fees required under 37 C.F.R. Section 1.16 and Section 1.17 and credit any overpayments to account no. 23-0925.		

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT	
Firm or Individual name	James E. Lake Reg. No. 44,854; Wells St. John P.S. (021567)
Signature	
Date	16 Jan 2004

CERTIFICATE OF TRANSMISSION/MAILING			
I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the date shown below.			
Typed or printed name			
Signature		Date	

This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

EL979977214
EL979977214



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 10/671,229
Filing Date September 24, 2003
Inventor..... Leonard Forbes
Assignee Micron Technology, Inc.
Group Art Unit 2811
Examiner Unknown
Attorney's Docket No. MI22-2272
Customer No. 021567
Title: Electronic Apparatus, Silicon-On-Insulator Integrated Circuits, and Fabrication
Methods

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -See Attached Form PTO-1449

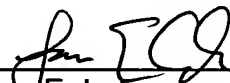
The Examiner's attention is directed to the references which are listed on the attached Form PTO-1449, copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

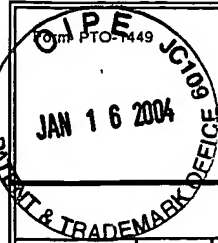
Citation of the referenced art is respectfully requested.

This Supplemental Information Disclosure Statement is being filed within three months of the filing date of the application or before the mailing date of a first Office Action, whichever occurs last. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 16 Jan 2004

By: 
James E. Lake
Reg. No. 44,854

		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2272		SERIAL NO. 10/671,229	
		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					
		APPLICANT Leonard Forbes				FILING DATE September 24, 2003	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AH						
	AI						
	AJ						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AK		C. Harendt et al. "Silicon on Insulator Material by Wafer Bonding," J. Electronic Materials, vol. 20, no. 3, pp. 267-277, March 1991				
	AL		S.M. Sze, "Physics of Semiconductor Devices," John Wiley & Sons, New York (1981), pgs. 850-851.				
	AM		J.B. Laksy, "Wafer Bonding for Silicon on Insulator Technologies," Appl. Phys. Letters, Vol. 48, No. 1, pp. 78-80, Jan. 1986.				
	AN		M. Breul et al., "Smart-Cut: a New Silicon on Insulator Material Technology Based on Hydrogen Implantation and Wafer Bonding," Proc. 1996 Int. Conf. On Solid State Devices and Materials, Japan. J. Appl. Phys., Part 1, Vol. 36, No. 3B, pp. 1636-41, 1996				
	AO		T. Suni et al., "Effects of Plasma Activation on Hydrophilic Bonding of Si and SiO ₂ ," J. Electrochem. Soc., Vol. 149, No. 6, pp. G348-51, June 2002.				
EXAMINER				DATE CONSIDERED			
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							